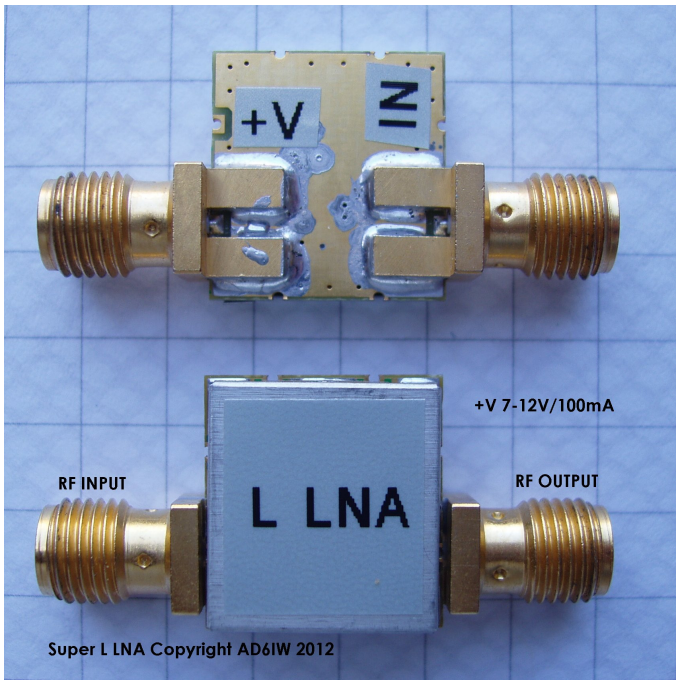
Ultra Low Noise and high linearity Amplifier for L Band with GaAs pHEMT MMIC

NEW

AD6IW@AD6IW.COM



Features:

800 - 1800MHz

NF

Noise Temp. 21 Kelvin
0.3dB @ 1296MHz
0.31dB @ 1420MHz
0.32dB @ 1575MHz
measured at 25 deg C

Gain

23dB +/- 1dB

IP3

High OIP3 performance
+35dBm @ 1296MHZ
IIP3 +12dBm @1296MHz

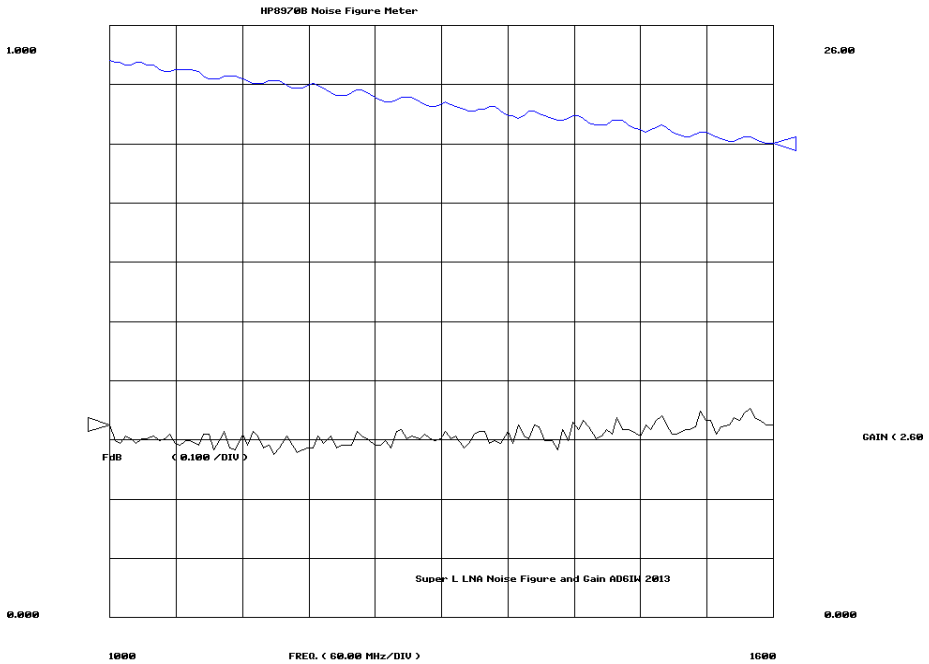
Max input power
+24dBm
Supply voltage:
7 to 15V, 80-100mA

Built in voltage regulator *

Option: LPF, HPF, bias T

Unconditional stable LNA

Input RL >10dB
Output RL 20dB



Noise Figure and Gain vs Frequency 1000 – 1600 MHz

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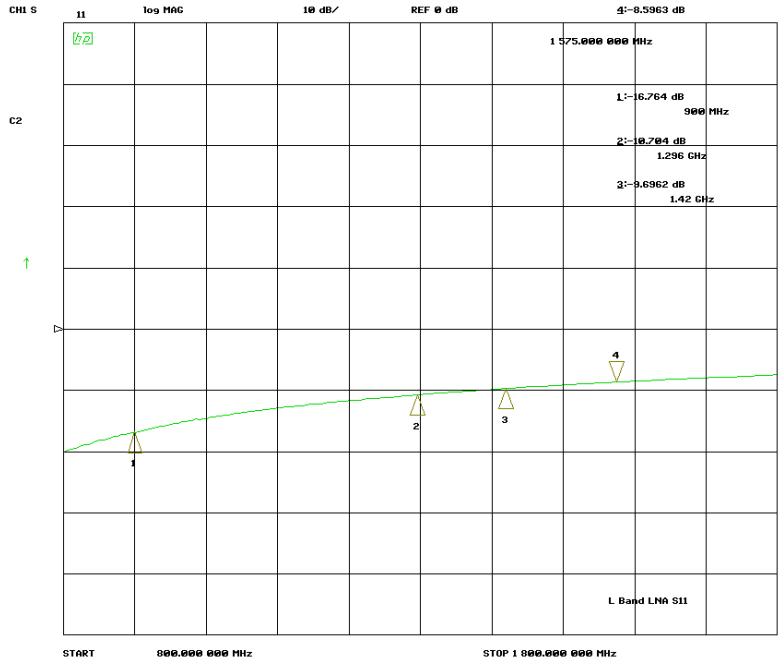
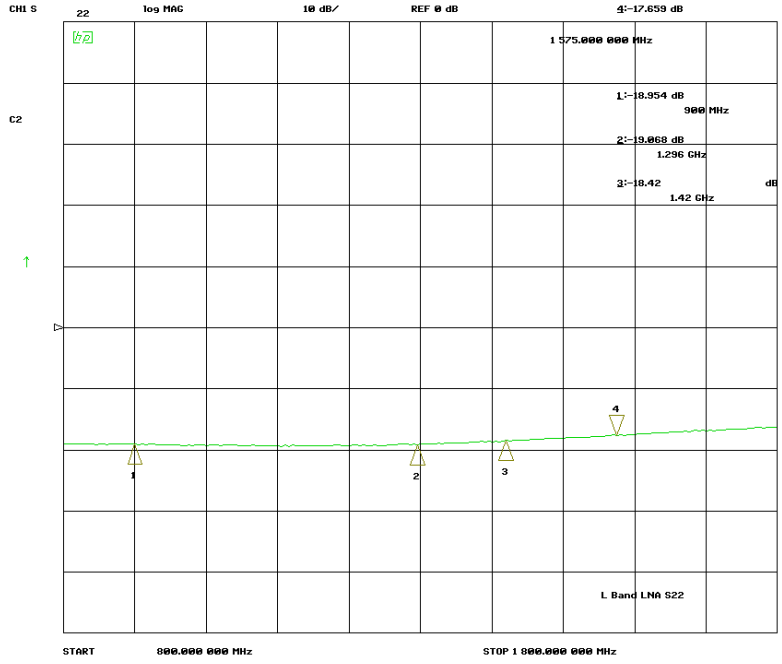


S11 Input Return Loss



S22 Output Return Loss

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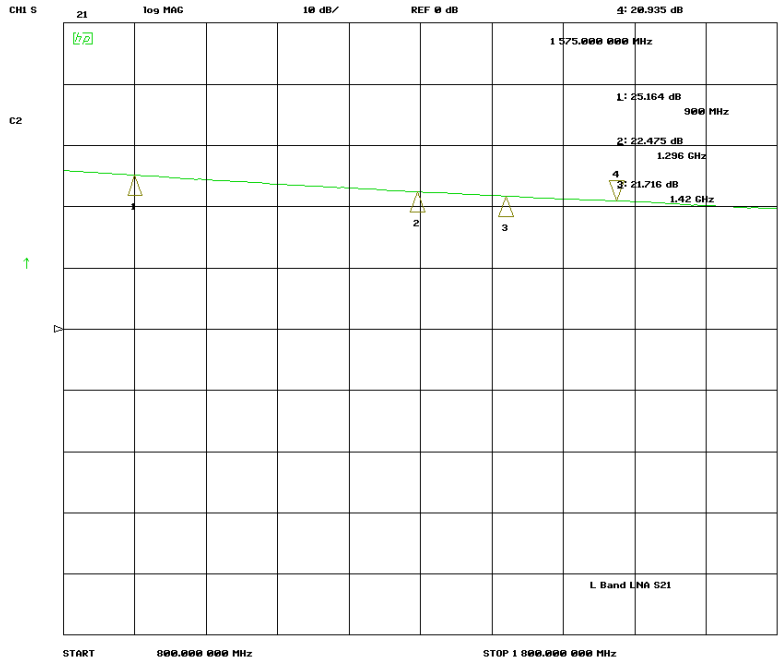
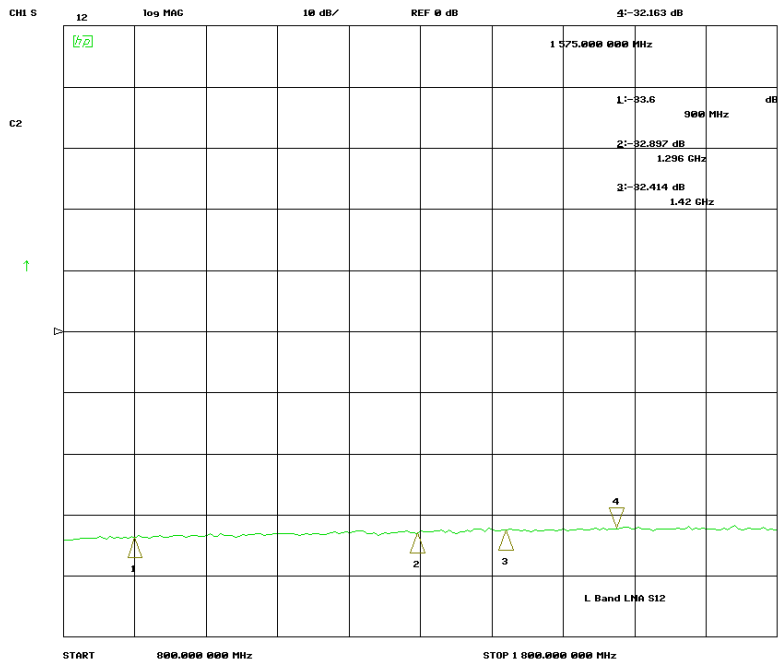


S21 Gain



S12 Isolation

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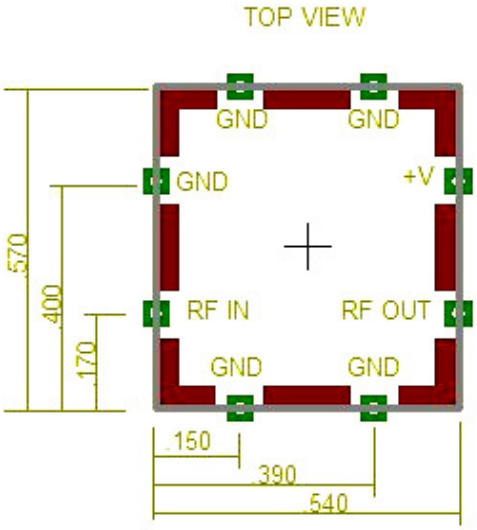
Dimensions:
33 x 15 x 7mm SMA
15 x 15 x 3.7 mm Module

Both SMA and SMD Module for PCB mount versions available



SMD Module PCB footprint, size in inches

***NOTE**
To keep LNA temperature low, and low noise figure it is recommended to:
Install LNA on small heat sink or chassis.
When supply voltage is 12V or higher install 56 Ohms ½ W resistor is series with V+.